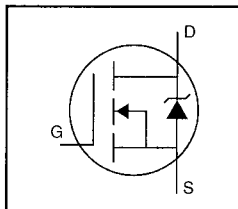


HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Logic-Level Gate Drive
- $R_{DS(on)}$ Specified at $V_{GS}=4V$ & $5V$
- $175^{\circ}C$ Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements



$$V_{DSS} = 60V$$

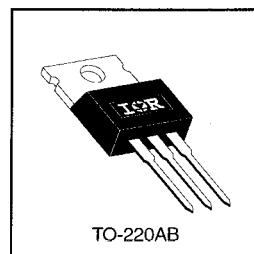
$$R_{DS(on)} = 0.028\Omega$$

$$I_D = 50^*A$$

Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



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Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^{\circ}C$	Continuous Drain Current, V_{GS} @ 5.0 V	50*	A
I_D @ $T_C = 100^{\circ}C$	Continuous Drain Current, V_{GS} @ 5.0 V	36	
I_{DM}	Pulsed Drain Current ①	200	
P_D @ $T_C = 25^{\circ}C$	Power Dissipation	150	W
	Linear Derating Factor	1.0	W/ $^{\circ}C$
V_{GS}	Gate-to-Source Voltage	± 10	V
E_{AS}	Single Pulse Avalanche Energy ②	400	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5	V/ns
T_J	Operating Junction and	-55 to +175	$^{\circ}C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.0	$^{\circ}C/W$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.070	—	$\text{V}/^\circ\text{C}$	Reference to 25°C , $I_D=1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.028	Ω	$V_{GS}=5.0\text{V}$, $I_D=31\text{A}$ ④
		—	—	0.039		
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$
g_{fs}	Forward Transconductance	23	—	—	S	$V_{DS}=25\text{V}$, $I_D=31\text{A}$ ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$ $V_{DS}=48\text{V}$, $V_{GS}=0\text{V}$, $T_J=150^\circ\text{C}$
		—	—	250		
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS}=10\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS}=-10\text{V}$
Q_g	Total Gate Charge	—	—	66	nC	$I_D=51\text{A}$
Q_{gs}	Gate-to-Source Charge	—	—	12		$V_{DS}=48\text{V}$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	43		$V_{GS}=5.0\text{V}$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD}=30\text{V}$ $I_D=51\text{A}$ $R_G=4.6\Omega$ $R_D=0.56\Omega$ See Figure 10 ④
t_r	Rise Time	—	230	—		
$t_{d(off)}$	Turn-Off Delay Time	—	42	—		
t_f	Fall Time	—	110	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	3300	—	pF	$V_{GS}=0\text{V}$ $V_{DS}=25\text{V}$ $f=1.0\text{MHz}$ See Figure 5
C_{oss}	Output Capacitance	—	1200	—		
C_{rss}	Reverse Transfer Capacitance	—	200	—		



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	50*	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	200		
V_{SD}	Diode Forward Voltage	—	—	2.5	V	$T_J=25^\circ\text{C}$, $I_S=51\text{A}$, $V_{GS}=0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	130	180	ns	$T_J=25^\circ\text{C}$, $I_F=51\text{A}$
Q_{rr}	Reverse Recovery Charge	—	0.84	1.3	μC	$di/dt=100\text{A}/\mu\text{s}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ② $V_{DD}=25\text{V}$, starting $T_J=25^\circ\text{C}$, $L=179\mu\text{H}$, $R_G=25\Omega$, $I_{AS}=51\text{A}$ (See Figure 12)
- ③ $I_{SD}\leq 51\text{A}$, $di/dt\leq 250\text{A}/\mu\text{s}$, $V_{DD}\leq V_{(BR)DSS}$, $T_J\leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

* Current limited by the package, (Die Current =51A)

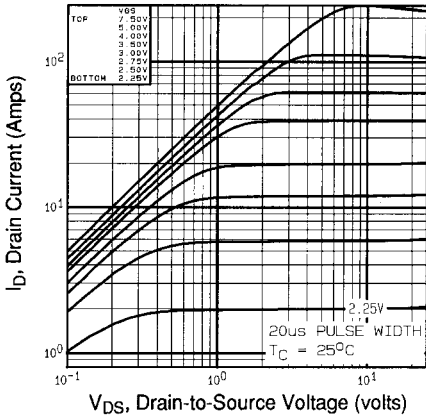


Fig 1. Typical Output Characteristics,
 $T_C=25^\circ\text{C}$

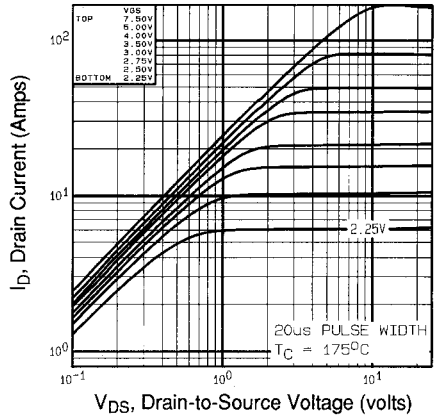


Fig 2. Typical Output Characteristics,
 $T_C=175^\circ\text{C}$

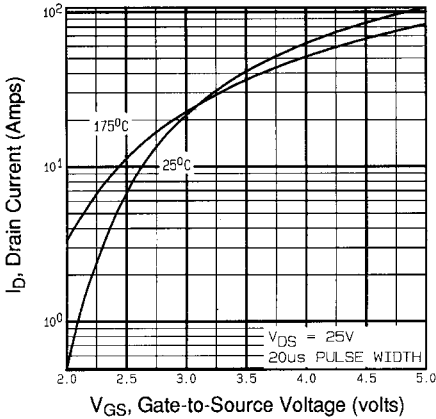


Fig 3. Typical Transfer Characteristics

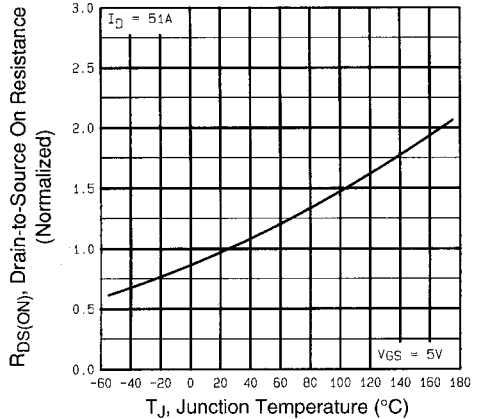


Fig 4. Normalized On-Resistance
Vs. Temperature

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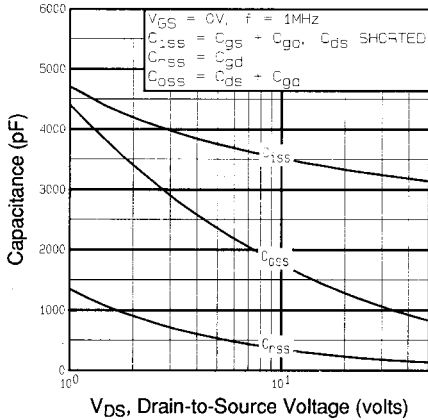


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

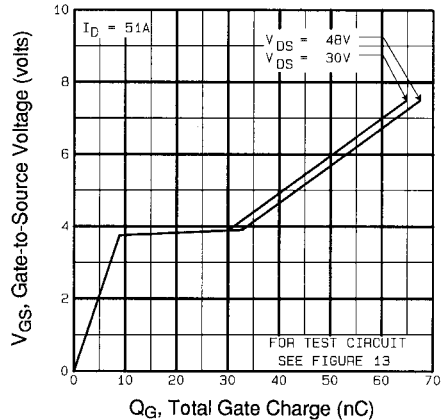


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

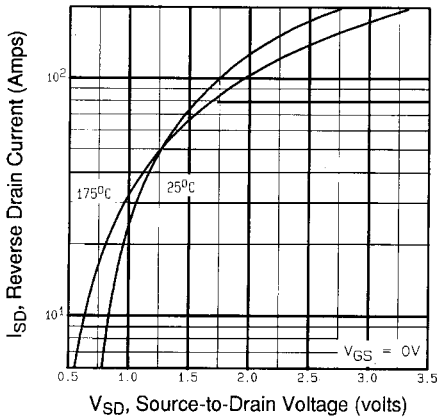


Fig 7. Typical Source-Drain Diode Forward Voltage

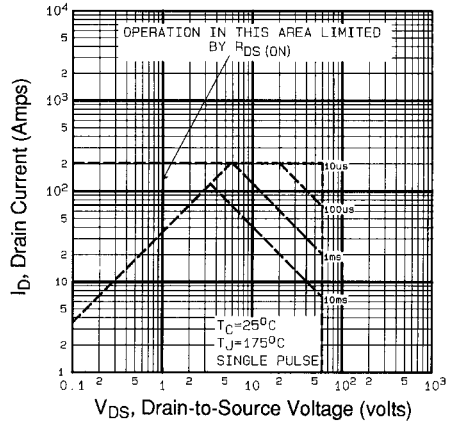


Fig 8. Maximum Safe Operating Area

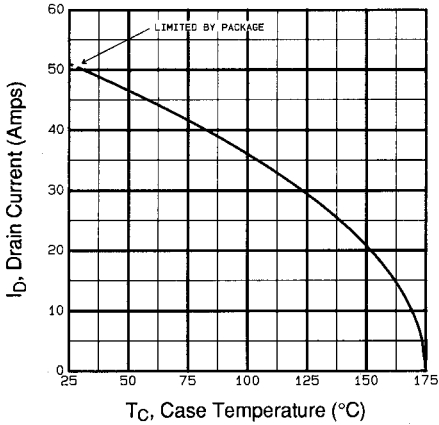


Fig 9. Maximum Drain Current Vs. Case Temperature

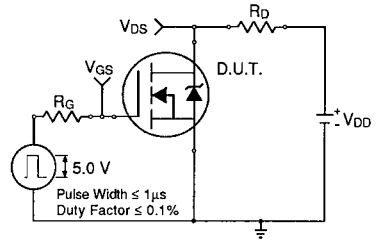


Fig 10a. Switching Time Test Circuit

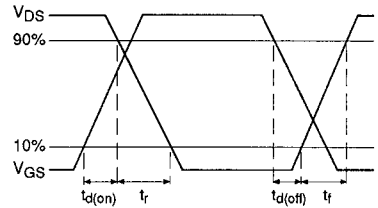


Fig 10b. Switching Time Waveforms

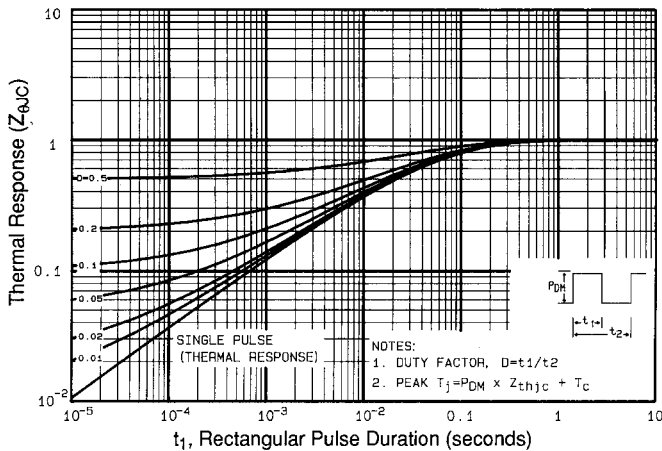


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

DATA SHEETS

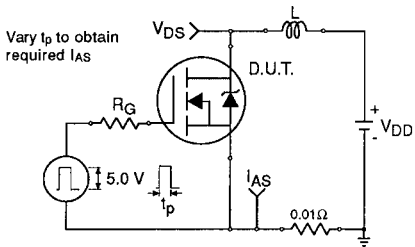


Fig 12a. Unclamped Inductive Test Circuit

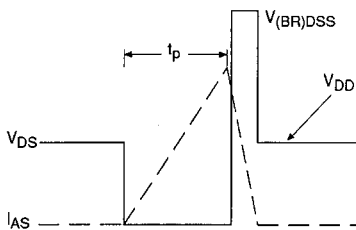


Fig 12b. Unclamped Inductive Waveforms

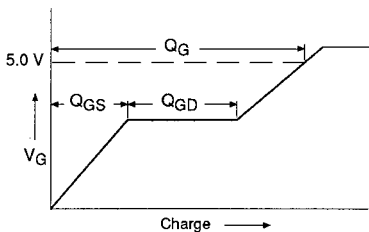


Fig 13a. Basic Gate Charge Waveform

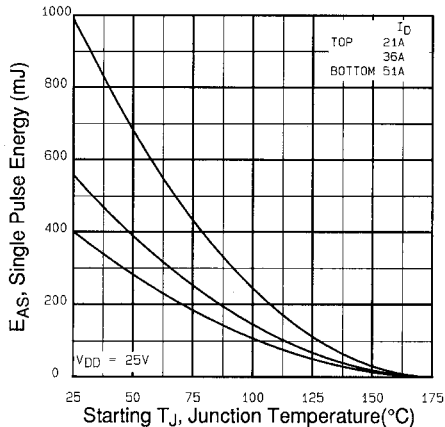


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

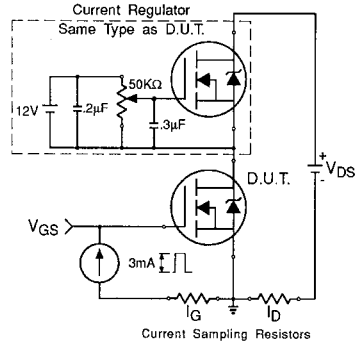


Fig 13b. Gate Charge Test Circuit

Appendix A: Figure 14, Peak Diode Recovery dv/dt Test Circuit – See page 1505

Appendix B: Package Outline Mechanical Drawing – See page 1509

Appendix C: Part Marking Information – See page 1516

Appendix E: Optional Leadforms – See page 1525